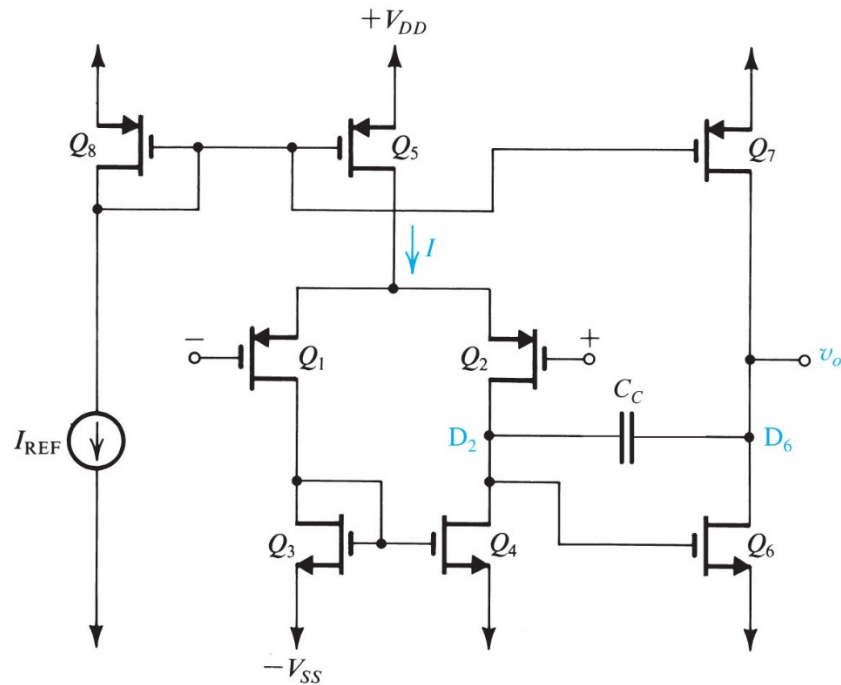


Homework 7 – Due 11/9/2016

Problems (not review questions): 9.113, 9.114



**Figure 9.40** Two-stage CMOS op-amp configuration.

Answers for **9.113**:  $W = 20 \mu\text{m}$ ,  $A_1 = -36 \text{ V/V}$ ,  $A_2 = -36 \text{ V/V}$ ,  $-1.25 \text{ V} \leq V_{\text{ICM}} \leq +0.25 \text{ V}$ ,  $-1.25 \text{ V} \leq v_o \leq +1.25 \text{ V}$

The results are summarized in the following table.

	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$	$Q_7$	$Q_8$
$I_D$ ( $\mu\text{A}$ )	112.5	112.5	112.5	112.5	225	225	225	225
$ V_{OV} $ (V)	0.25	0.25	0.25	0.25	0.25	0.25	0.25	0.25
$ V_{GS} $ (V)	1.0	1.0	1.0	1.0	1.0	1.0	1.0	1.0
$g_m$ (mA/V)	0.9	0.9	0.9	0.9	1.8	1.8	1.8	1.8
$r_o$ (k $\Omega$ )	80	80	80	80	40	40	40	40

#### EE381 HOMEWORK FORMAT GUIDELINES

Things to remember

- 1) Re-Draw the Circuit on your homework sheet.
- 2) Show all work.
- 3) Final answer should be in decimal form.
- 4) Final answers should be boxed.
- 5) Your name should be on every page.

9.113 Refer to Fig. 9.40.

$W_6$  can be determined using Eq. (9.172):

$$\frac{(W/L)_6}{(W/L)_4} = 2 \frac{(W/L)_7}{(W/L)_5}$$

$$\frac{(W/0.5)_6}{(10/0.5)} = 2 \frac{(60/0.5)}{(60/0.5)}$$

$$\Rightarrow W_6 = 20 \mu\text{m}$$

For all devices we can evaluate  $I_D$  as follows:

$$I_{D8} = I_{\text{REF}} = 225 \mu\text{A}$$

$$I_{D5} = I_{\text{REF}} \frac{(W/L)_5}{(W/L)_8} = I_{\text{REF}} = 225 \mu\text{A}$$

$$I = I_{D5} = 225 \mu\text{A}$$

$$I_{D1} = I_{D2} = \frac{1}{2} I_{D5} = 112.5 \mu\text{A}$$

$$I_{D3} = I_{D4} = I_{D1} = 112.5 \mu\text{A}$$

$$I_{D6} = I_{D7} = I_{\text{REF}} = 225 \mu\text{A}$$

With  $I_D$  in each device known, we can use

$$I_{Di} = \frac{1}{2} \mu C_{ox} \left( \frac{W}{L} \right)_i |V_{OV}|^2$$

to determine  $|V_{OV}|$  and then

$$|V_{GS}| = |V_{OV}| + |V_t|$$

The values of  $g_{mi}$  and  $r_{oi}$  can then be determined from

$$g_{mi} = \frac{2I_{Di}}{|V_{OV}|}$$

$$r_{oi} = \frac{|V_A|}{I_{Di}}$$

The results are summarized in the following table.

	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$	$Q_7$	$Q_8$
$I_D$ ( $\mu\text{A}$ )	112.5	112.5	112.5	112.5	225	225	225	225
$ V_{OV} $ (V)	0.25	0.25	0.25	0.25	0.25	0.25	0.25	0.25
$ V_{GS} $ (V)	1.0	1.0	1.0	1.0	1.0	1.0	1.0	1.0
$g_m$ (mA/V)	0.9	0.9	0.9	0.9	1.8	1.8	1.8	1.8
$r_o$ (k $\Omega$ )	80	80	80	80	40	40	40	40

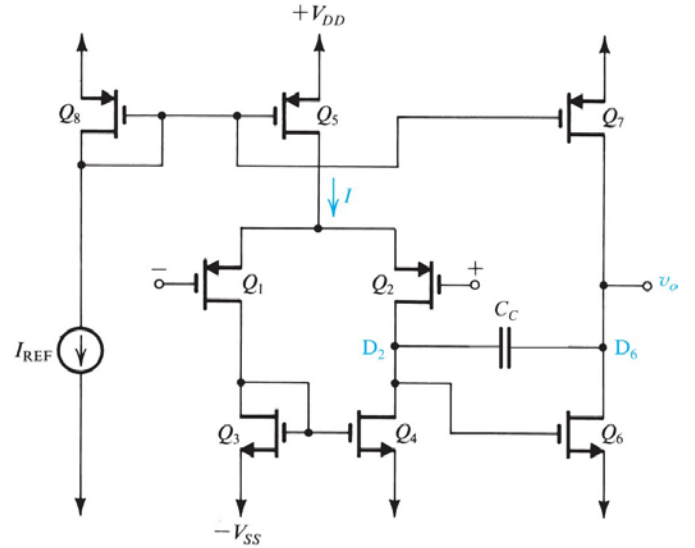


Figure 9.40 Two-stage CMOS op-amp configuration.

$$A_1 = -g_{m1}(r_{o2} \parallel r_{o4})$$

$$= -0.9 \times (80 \parallel 80) = -36 \text{ V/V}$$

$$A_2 = -g_{m6}(r_{o6} \parallel r_{o7})$$

$$= -1.8 \times (40 \parallel 40) = -36 \text{ V/V}$$

$$A_0 = A_1 A_2 = -36 \times -36 = 1296 \text{ V/V}$$

The upper limit of  $V_{ICM}$  is determined by the need to keep  $Q_5$  in saturation, thus

$$V_{ICM\max} = V_{DD} - |V_{OV5}| - |V_{SG1}|$$

$$= 1.5 - 0.25 - 1 = +0.25 \text{ V}$$

The lower limit of  $V_{ICM}$  is determined by the need to keep  $Q_1$  and  $Q_2$  in saturation, thus

$$V_{ICM\min} = V_{G3} - |V_t|$$

$$= -V_{SS} + |V_{GS3}| - |V_t|$$

$$= -1.5 + 1 - 0.75 = -1.25 \text{ V}$$

Thus

$$-1.25 \text{ V} \leq V_{ICM} \leq +0.25 \text{ V}$$

The output voltage range is

$$-V_{SS} + V_{OV6} \leq v_O \leq V_{DD} - |V_{OV7}|$$

that is,

$$-1.25 \text{ V} \leq v_O \leq +1.25 \text{ V}$$

9.114

$$(a) I_{D1} = I_{D2} = 100 = \frac{1}{2} \mu_n C_{ox} \left( \frac{W}{L} \right)_{1,2} V_{OV}^2$$

$$100 = \frac{1}{2} \times 400 \times \left( \frac{W}{L} \right)_{1,2} \times 0.04$$

$$\Rightarrow \left( \frac{W}{L} \right)_1 = \left( \frac{W}{L} \right)_2 = 12.5$$

$$I_{D3} = I_{D4} = 100 = \frac{1}{2} \mu_p C_{ox} \left( \frac{W}{L} \right)_{3,4} |V_{OV}|^2$$

$$100 = \frac{1}{2} \times 100 \times \left( \frac{W}{L} \right)_{3,4} \times 0.04$$

$$\Rightarrow \left( \frac{W}{L} \right)_3 = \left( \frac{W}{L} \right)_4 = 50$$

$$I_{D5} = I_{D7} = I_{D8} = 200 \mu\text{A}$$

Thus

$$200 = \frac{1}{2} \mu_n C_{ox} \left( \frac{W}{L} \right)_{5,7,8} V_{OV}^2$$

$$= \frac{1}{2} \times 400 \times \left( \frac{W}{L} \right)_{5,7,8} \times 0.04$$

$$\left( \frac{W}{L} \right)_5 = \left( \frac{W}{L} \right)_7 = \left( \frac{W}{L} \right)_8 = 25$$

$$I_{D6} = 200 = \frac{1}{2} \mu_p C_{ox} \left( \frac{W}{L} \right)_6 |V_{OV}|^2$$

$$200 = \frac{1}{2} \times 100 \times \left( \frac{W}{L} \right)_6 \times 0.04$$

$$\left( \frac{W}{L} \right)_6 = 100$$

The results are summarized in the following table:

Transistor	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$	$Q_7$	$Q_8$
$W/L$	12.5	12.5	50	50	25	100	25	25

Ideally, the dc voltage at the output is zero.

(b) The upper limit of  $V_{ICM}$  is determined by the need to keep  $Q_1$  and  $Q_2$  in saturation, thus

$$\begin{aligned} V_{ICM\max} &= V_{D1} + V_t \\ &= V_{DD} - |V_{SG4}| + V_t \\ &= 0.9 - |V_t| - |V_{OV4}| + V_t \\ &= 0.9 - 0.2 = +0.7 \text{ V} \end{aligned}$$

The lower limit of  $V_{ICM}$  is determined by the need to keep  $Q_5$  in saturation,

$$\begin{aligned} V_{ICM\min} &= -0.9 + |V_{OV5}| + |V_{GS1}| \\ &= -0.9 + 0.2 + 0.2 + 0.4 = -0.1 \text{ V} \end{aligned}$$

Thus

$$-0.1 \text{ V} \leq V_{ICM} \leq +0.7 \text{ V}$$

$$(c) v_{O\max} = V_{DD} - |V_{OV6}|$$

$$= 0.9 - 0.2 = +0.7 \text{ V}$$

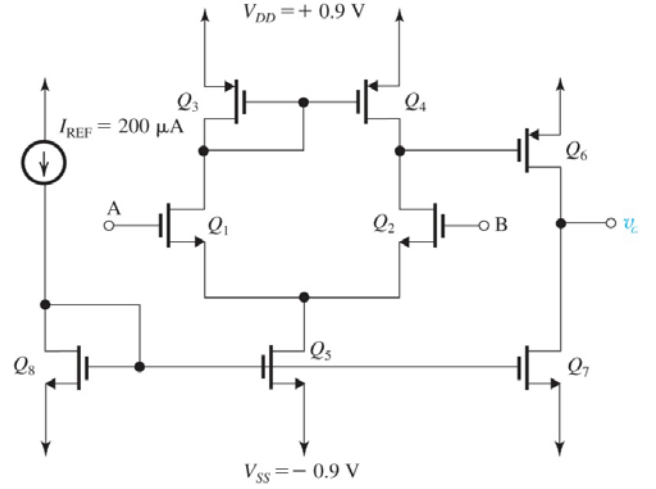


Figure P9.114

$$v_{O\min} = -V_{SS} + |V_{OV7}|$$

$$= -0.9 + 0.2 = -0.7 \text{ V}$$

Thus

$$-0.7 \text{ V} \leq v_O \leq +0.7 \text{ V}$$

$$(d) A_1 = -g_{m1,2}(r_{o2} \parallel r_{o4})$$

where

$$g_{m1,2} = \frac{2 \times 0.1}{0.2} = 1 \text{ mA/V}$$

$$r_{o2} = r_{o4} = \frac{|V_A|}{0.1 \text{ mA}} = \frac{6}{0.1} = 60 \text{ k}\Omega$$

$$A_1 = -1 \times (60 \parallel 60) = -30 \text{ V/V}$$

$$A_2 = -g_{m6}(r_{o6} \parallel r_{o7})$$

where

$$g_{m6} = \frac{2 \times 0.2}{0.2} = 2 \text{ mA/V}$$

$$r_{o6} = r_{o7} = \frac{|V_A|}{0.2} = \frac{6}{0.2} = 30 \text{ k}\Omega$$

$$A_2 = -2 \times (30 \parallel 30) = -30 \text{ V/V}$$

$$A_0 = A_1 A_2 = 30 \times 30 = 900 \text{ V/V}$$